

# **BUK662R7-55C**

## N-channel TrenchMOS intermediate level FET

Rev. 01 — 7 September 2010

**Product data sheet** 

### 1. Product profile

#### 1.1 General description

Intermediate level gate drive N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using advanced TrenchMOS technology. This product has been designed and qualified to the appropriate AEC Q101 standard for use in high performance automotive applications.

#### 1.2 Features and benefits

- AEC Q101 compliant
- Suitable for intermediate level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

#### 1.3 Applications

- 12 V and 24 V Automotive systems
- Electric and electro-hydraulic power steering
- Motors, lamps and solenoid control
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$		-	-	55	V
I <sub>D</sub>	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C};$ see Figure 1	[1]	-	-	120	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	-	306	W
Static characteristics							
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 11}}{\text{ or } 100 \text{ c}}$		-	2.3	2.7	mΩ



Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Avalanche	ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$I_D$ = 120 A; $V_{sup} \le 55$ V; $R_{GS} = 50 \Omega$ ; $V_{GS} = 10$ V; $T_{j(init)} = 25 ^{\circ}C$ ; unclamped	-	-	724	mJ
Dynamic ch	naracteristics					
$Q_{GD}$	gate-drain charge	$I_D$ = 25 A; $V_{DS}$ = 44 V; $V_{GS}$ = 10 V; see <u>Figure 13</u> ; see <u>Figure 14</u>	-	75	-	nC

<sup>[1]</sup> Continuous current is limited by package.

## 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		D.
2	D	Drain	mb	B
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT404 (D2PAK)	

## 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK662R7-55C	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

## 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	55	V
$V_{GS}$	gate-source voltage	DC	<u>[1]</u>	-16	16	V
		Pulsed	[2]	-20	20	V
I <sub>D</sub>	drain current	$T_{mb} = 25  ^{\circ}C; V_{GS} = 10  V; \text{see } \frac{\text{Figure 1}}{}$	[3]	-	120	Α
		$T_{mb} = 100 ^{\circ}\text{C}$ ; $V_{GS} = 10 \text{V}$ ; see Figure 1	[3]	-	120	Α
I <sub>DM</sub>	peak drain current	$T_{mb}$ = 25 °C; $t_p \le 10 \mu s$ ; pulsed; see Figure 3		-	907	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	306	W
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drain	diode					
Is	source current	T <sub>mb</sub> = 25 °C	[3]	-	120	Α
I <sub>SM</sub>	peak source current	$t_p \le 10 \ \mu s$ ; pulsed; $T_{mb} = 25 \ ^{\circ}C$		-	907	Α
Avalanche rug	ggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$I_D$ = 120 A; $V_{sup}$ ≤ 55 V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; unclamped		-	724	mJ
E <sub>DS(AL)R</sub>	repetitive drain-source avalanche energy		[4][5][6]	-	-	J

<sup>[1] -16</sup>V accumulated duration not to exceed 168 hrs.

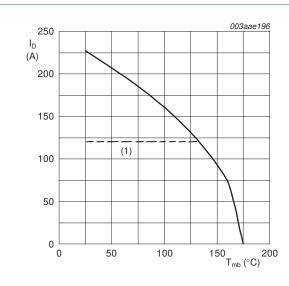
<sup>[2]</sup> Accumulated pulse duration not to exceed 5mins.

<sup>[3]</sup> Continuous current is limited by package.

<sup>[4]</sup> Single-pulse avalanche rating limited by maximum junction temperature of 175  $^{\circ}$ C.

<sup>[5]</sup> Repetitive avalanche rating limited by an average junction temperature of 170 °C.

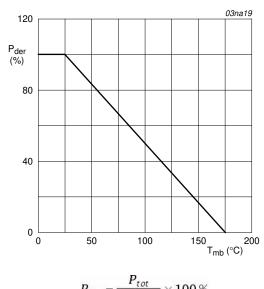
<sup>[6]</sup> Refer to application note AN10273 for further information.



 $V_{GS} \ge 10\,V$ 

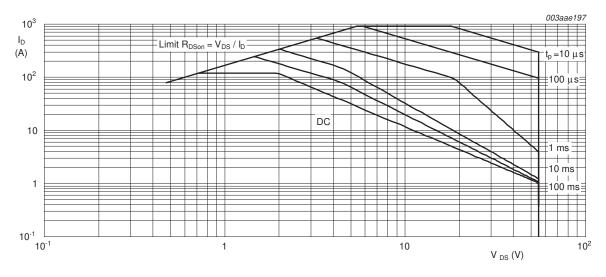
(1) Capped at 120 A due to package.

Continuous drain current as a function of mounting base temperature



$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

Fig 2. Normalized total power dissipation as a function of mounting base temperature



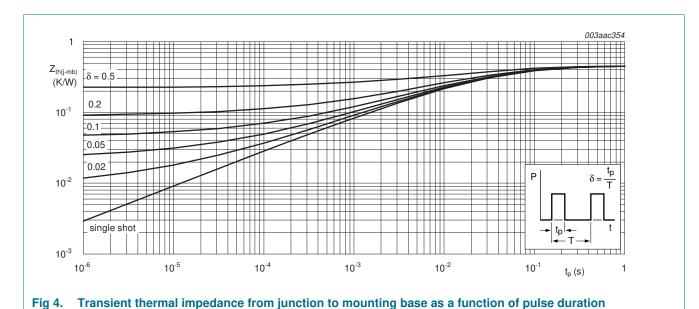
 $T_{mb} = 25$  °C;  $I_{DM}$  is a single pulse

Safe operating area; continuous and peak drain currents as a function of drain-source voltage Fig 3.

### 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	0.45	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	vertical in free air	-	60	-	K/W



## 6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V <sub>(BR)DSS</sub>	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ °C}$	55	-	-	٧
	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	50	-	-	٧
( )	gate-source threshold voltage	$I_D = 1 \text{ mA}$ ; $V_{DS} = V_{GS}$ ; $T_j = 25 \text{ °C}$ ; see <u>Figure 9</u> ; see <u>Figure 10</u>	1.8	2.3	2.8	V
		$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = -55 °C; see <u>Figure 10</u>	-	-	3.3	V
		$I_D$ = 2.5 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 175 °C; see <u>Figure 10</u>	0.8	-	-	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μΑ
		$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	1	μΑ
I <sub>GSS</sub>	gate leakage current	$V_{DS} = 0 \text{ V}; V_{GS} = 20 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nΑ
		$V_{DS} = 0 \text{ V}; V_{GS} = -20 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
Doon	drain-source on-state resistance	$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see <u>Figure 11</u>	-	2.9	3.8	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see Figure 11	-	2.3	2.7	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see Figure 11	-	3.2	4.4	mΩ
		$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 175 °C; see <u>Figure 12</u> ; see <u>Figure 11</u>	-	-	6	mΩ
Dynamic o	characteristics					
$Q_{G(tot)}$	total gate charge	$I_D = 25 \text{ A}$ ; $V_{DS} = 44 \text{ V}$ ; $V_{GS} = 5 \text{ V}$ ; see Figure 13; see Figure 14	-	146	-	nC
		$I_D = 25 \text{ A}; V_{DS} = 44 \text{ V}; V_{GS} = 10 \text{ V};$	-	258	-	nC
Q <sub>GS</sub>	gate-source charge	see Figure 13; see Figure 14	-	35	-	nC
Q <sub>GD</sub>	gate-drain charge		-	75	-	nC
C <sub>iss</sub>	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$	-	11430	15300	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; see <u>Figure 15</u>	-	1100	1320	pF
C <sub>rss</sub>	reverse transfer capacitance		-	772	1060	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 45 \text{ V}; R_L = 1.8 \Omega; V_{GS} = 10 \text{ V};$	-	61	-	ns
r	rise time	$R_{G(ext)} = 10 \Omega$	-	101	-	ns
d(off)	turn-off delay time		-	450	-	ns
t <sub>f</sub>	fall time		-	186	-	ns
L <sub>D</sub>	internal drain inductance	from upper edge of drain mounting base to centre of die; $T_j = 25$ °C	-	3.5	-	nΗ
L <sub>S</sub>	internal source inductance	from source lead to source bond pad; $T_i = 25 ^{\circ}\text{C}$	-	7.5	-	nΗ

 $V_{GS}(V) = 3.6$ 

3.4

3.2

#### N-channel TrenchMOS intermediate level FET

Table 6. Characteristics ... continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-drai	n diode					
V <sub>SD</sub>	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C};$ see <u>Figure 16</u>	-	0.85	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 20 \text{ A}$ ; $dI_S/dt = -100 \text{ A/}\mu\text{s}$ ; $V_{GS} = 0 \text{ V}$ ;	-	67	-	ns
Q <sub>r</sub>	recovered charge	$V_{DS} = 25 \text{ V}$	-	176	-	nC

100

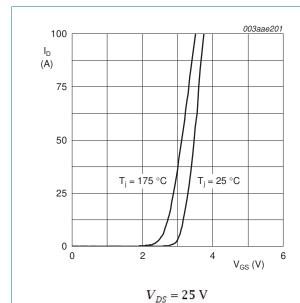


Fig 5. Transfer characteristics: drain current as a function of gate-source voltage; typical values

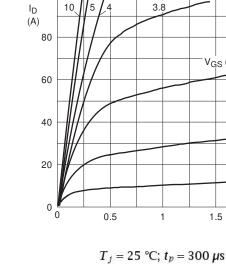


Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values

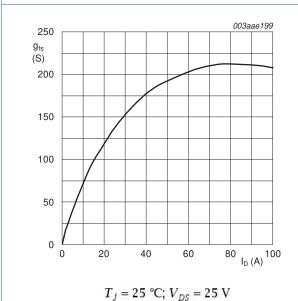


Fig 7. Forward transconductance as a function of drain current; typical values

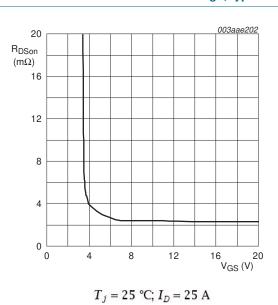


Fig 8. Drain-source on-state resistance as a function of gate-source voltage; typical values

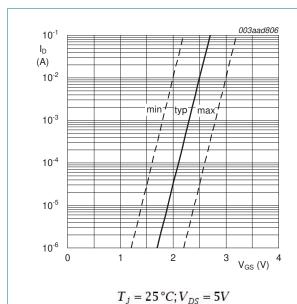


Fig 9. Sub-threshold drain current as a function of gate-source voltage

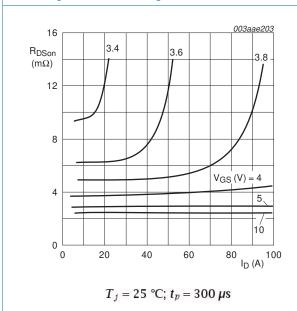


Fig 11. Drain-source on-state resistance as a function of drain current; typical values

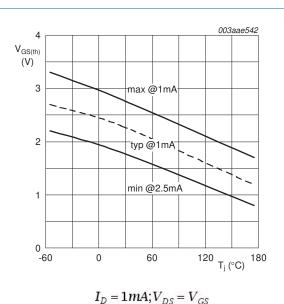


Fig 10. Gate-source threshold voltage as a function of junction temperature

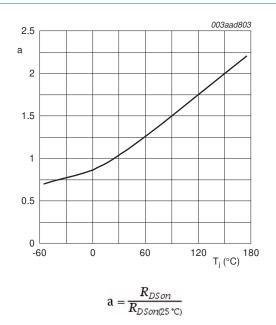
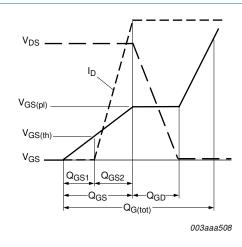


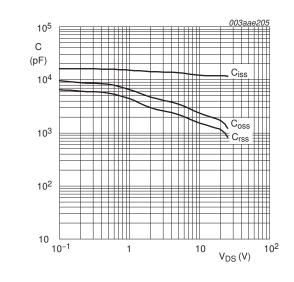
Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature



 $T_j = 25$  °C;  $I_D = 25$  A

Fig 13. Gate charge waveform definitions





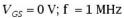


Fig 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

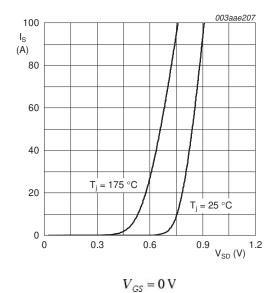


Fig 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

### 7. Package outline

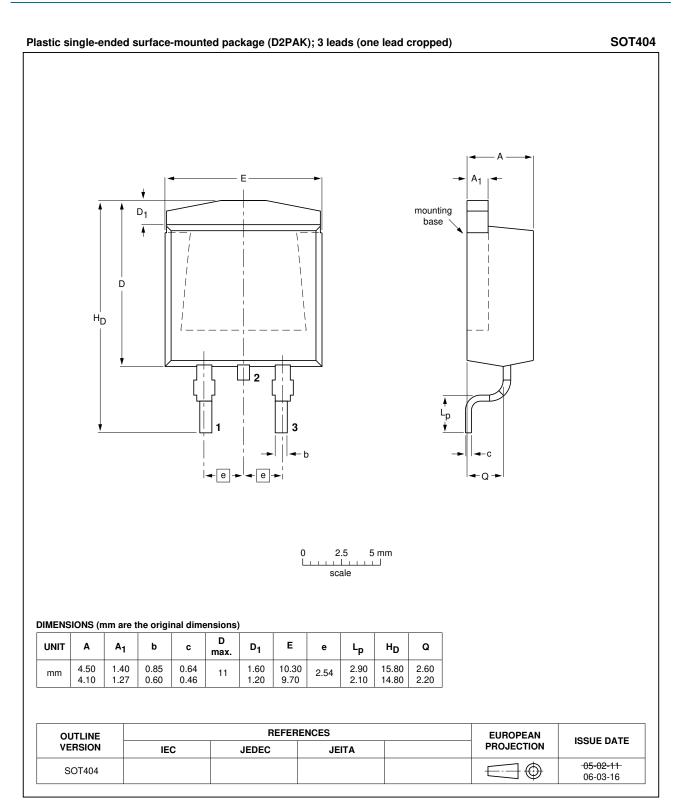


Fig 17. Package outline SOT404 (D2PAK)

BUK662R7-55C

#### N-channel TrenchMOS intermediate level FET

## 8. Revision history

#### Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK662R7-55C v.1	20100907	Product data sheet	-	-

### 9. Legal information

#### 9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design
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### 11. Contents

1	Product profile
1.1	General description
1.2	Features and benefits
1.3	Applications
1.4	Quick reference data1
2	Pinning information2
3	Ordering information2
4	Limiting values
5	Thermal characteristics5
6	Characteristics6
7	Package outline
8	Revision history11
9	Legal information12
9.1	Data sheet status
9.2	Definitions12
9.3	Disclaimers
9.4	Trademarks13
10	Contact information 13